

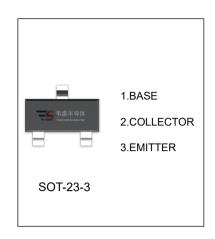
## 2SB1116 TRANSISTOR (PNP)

## **FEATURES**

• High Collector Power Dissipation

MAXIMUM RATINGS (T<sub>A</sub>=25°C unless otherwise noted)

Symbol	Parameter	Value	Únit
V <sub>CBO</sub>	Collector-Base Voltage	-60	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-50	V
V <sub>EBO</sub>	Emitter-Base Voltage	-6	V
Ic	Collector Current -Continuous	-1	Α
Pc	Collector Power Dissipation	0.35	W
$T_J, T_{stg}$	Operation Junction and Storage Temperature Range	-55-150	℃



**ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)** 

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =-100μA,I <sub>E</sub> =0	-60			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =-1mA,I <sub>B</sub> =0	-50			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =-100μA,I <sub>C</sub> =0	-6			V
Collector cut-off current	I <sub>CBO</sub>	$V_{CB}$ =-60 $V$ , $I_E$ =0			-0.1	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =-6V,I <sub>C</sub> =0			-0.1	μA
DC ourrent gain	h <sub>FE(1)</sub>	V <sub>CE</sub> =-2V,I <sub>C</sub> =-0.1A	135		600	
DC current gain	h <sub>FE(2)</sub>	V <sub>CE</sub> =-2V,I <sub>C</sub> =-1A	81			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-1A,I <sub>B</sub> =-50mA			-0.3	V
Base -emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =-1A,I <sub>B</sub> =-50mA			-1.2	V
Base -emitter voltage	V <sub>BE</sub>	V <sub>CE</sub> =-2V,I <sub>C</sub> =-0.05A	-0.6		-0.7	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =-2V,I <sub>C</sub> =-0.1A	70			MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =-10V,I <sub>E</sub> =0,f=1MHz		25		pF
Turn-on time	t <sub>on</sub>			0.07		us
Storage time	t <sub>s</sub>	$V_{CC}$ =-10V, $I_{C}$ =-0.1A, $I_{B1}$ =- $I_{B2}$ =-0.01A, $V_{BE(Off)}$ =2to3V		0.7		us
Fall time	t <sub>f</sub>			0.07		us

## CLASSIFICATION OF h<sub>FE(1)</sub>

Rank	L	К	U
Range	135-270	200-400	300-600



